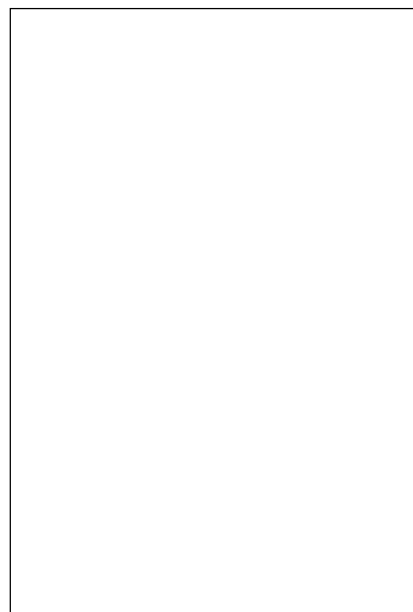


**DESCRIPTION:**

The JR0805H SCR with the parallel resistor between Gate and Cathode, $R_{GK}=10\sim 80k$ is especially recommended for use on straight hair, igniter, anion generator, etc. Package TO-251 is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	600	V
I_{GT}	200	μA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage ($T_j=25^\circ C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^\circ C$)	V_{RRM}	600	V
Average on-state current ($T_c=76^\circ C$)	$I_{T(AV)}$	5	A
RMS on-state current ($T_c=76^\circ C$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current ($t_p=10ms, T_j=25^\circ C$)	I_{TSM}	80	A
Non repetitive surge peak on-state current ($t_p=8.3ms, T_j=25^\circ C$)		88	
I^2t value for fusing ($t_p=10ms, T_j=25^\circ C$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2 I_{GT}, f=100Hz, T_j=125^\circ C$)	di/dt	50	$A/\mu s$
Peak gate current ($t_p=20\mu s, T_j=125^\circ C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=125^\circ C$)	$P_{G(AV)}$	1	W

Peak gate power	P_{GM}	5	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

NOTE 1: When we parallel connect a 1K resistor between Gate and Cathode, the T_j can reach 125 ; if without this resistor, the T_j only can reach 110 .

ELECTRICAL CHARACTERISTICS

unless otherwise specified

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	$V_D=12V R_L=33$	-	-	200	μA
V_{GT}		-	-	0.8	V
V_{GD}	$V_D=V_{DRM} T_j=125$	0.2	-	-	V
I_L	$I_G=1.2 I_{GT}$	-	-	6	mA
I_H	$I_T=0.1A$	-	-	5	mA
dV/dt	$V_D=400V T_j=125 R_{GK}=1K$	50	-	-	V/ μs
	$V_D=400V T_j=125 R_{GK}=220$	250	-	-	
t_{on}	$I_G=10mA I_A=20mA I_R=2mA$ $T_j=25$	-	2	-	μs
t_{off}		-	50	-	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=16A t_p=380\mu s$	$T_j=25$	1.55	V
V_{TO}	Threshold voltage	$T_j=125$	0.79	V
R_D	Dynamic resistance	$T_j=125$	0.02	
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (DC)	4.5	$/W$
$R_{th(j-a)}$	junction to ambient (DC)	120	$/W$

ORDERING INFORMATION

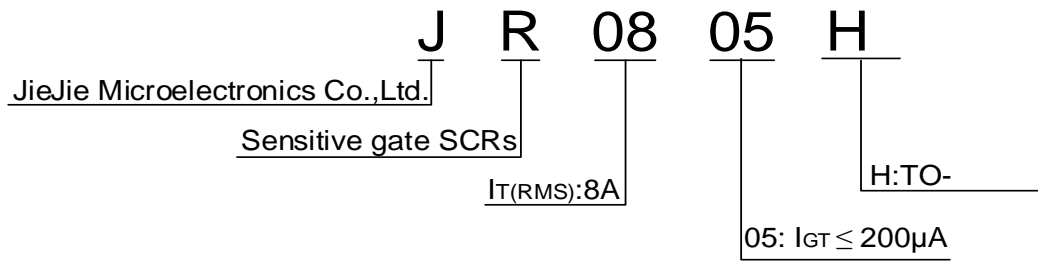


FIG.1 Maximum power dissipation versus RMS on-state current

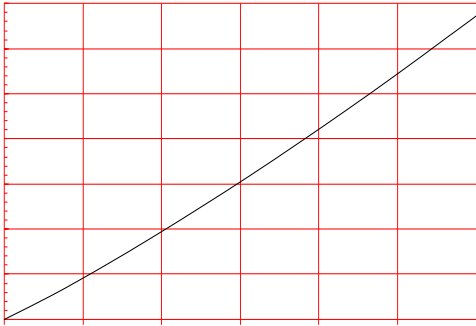


FIG.2: RMS on-state current versus case temperature

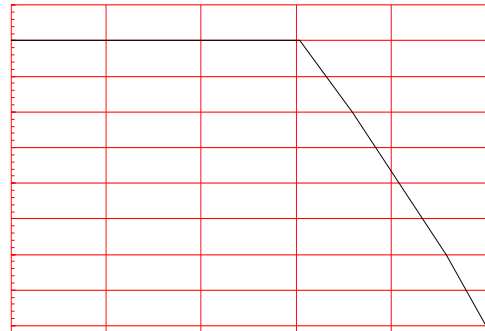


FIG.3: Surge peak on-state current versus number of cycles

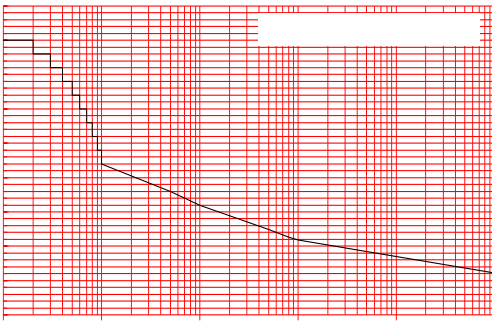


FIG.4: On-state characteristics

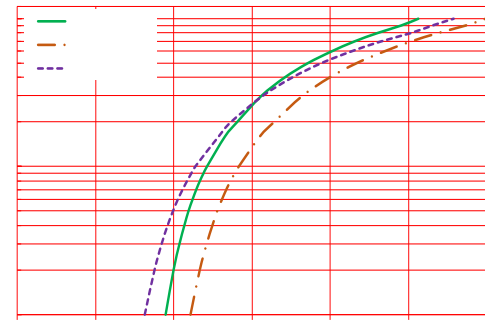


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)

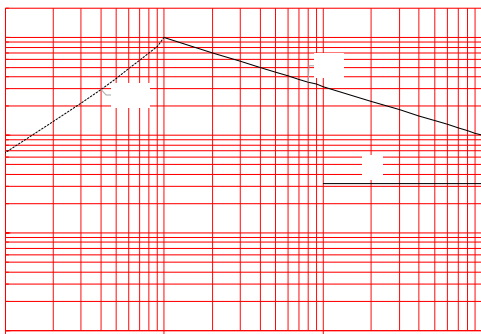


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

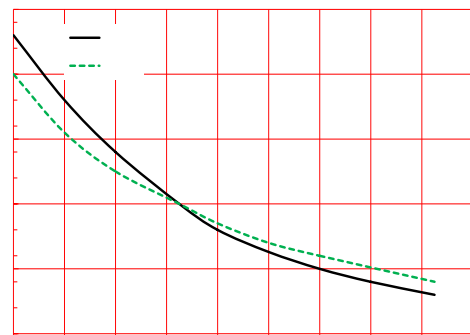
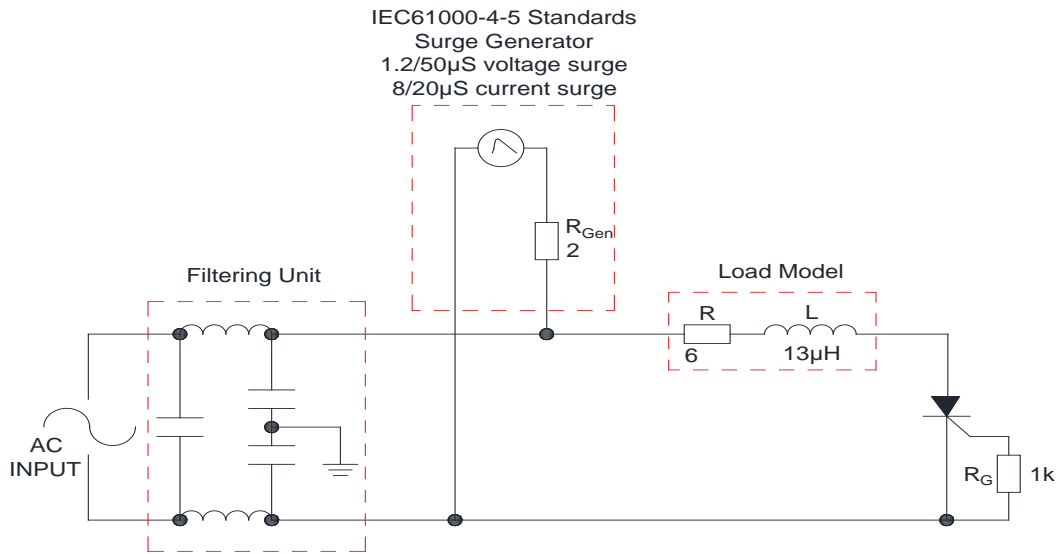


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



SHAPING AND SOLDERING PARAMETERS

Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{R_{RRM}} (V)	IGT(μA)	Package	Base qty. (pcs)	Delivery mode
JR0805H	600	200	TO-251	80	Tube

Document Revision History

Date	Revision	
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PACKAGE MECHANICAL DATA

